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Front Matter: Volume 8327

, "Front Matter: Volume 8327," Proc. SPIE 8327, Design for Manufacturability through Design-Process Integration VI, 832701 (17 April 2012); doi: 10.1117/12.928432

Event: SPIE Advanced Lithography, 2012, San Jose, California, United States

PROCEEDINGS OF SPIE

Design for Manufacturability through Design-Process Integration VI

**Mark E. Mason
John L. Sturtevant**
Editors

**15–16 February 2012
San Jose, California, United States**

Sponsored and Published by
SPIE

Volume 8327

Proceedings of SPIE, 0277-786X, v. 8327

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Design for Manufacturability through Design-Process Integration VI, edited by Mark E. Mason, John L. Sturtevant,
Proc. of SPIE Vol. 8327, 832701 · © 2012 SPIE · CCC code: 0277-786X/12/\$18 · doi: 10.1117/12.928432

Proc. of SPIE Vol. 8327 832701-1

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Please use the following format to cite material from this book:

Author(s), "Title of Paper," in *Design for Manufacturability through Design-Process Integration VI*, edited by Mark E. Mason, John L. Sturtevant, Proceedings of SPIE Vol. 8327 (SPIE, Bellingham, WA, 2012) Article CID Number.

ISSN 0277-786X

ISBN 9780819489838

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

SPIE.org

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Printed in the United States of America.

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Introduction

I am very excited to be writing this introduction to the Proceedings of the 2012 SPIE conference on Design for Manufacturability through Design-Process Integration (DfM-DPI).

This marks the sixth year of the DfM-DPI conference, and I could not be happier with the quality of work that was submitted for publication this year. Experts from around the world participated representing various segments of the Semiconductor industry and academia. Once again, we enjoyed strong representation from Europe, Asia, and America. We even saw an increase in participation (as measured by paper submissions) over last year, indicating that the industry remains heavily focused on Design for Manufacturability.

Our keynote speakers this year were simply outstanding. Well recognized as premier experts in their field, the presenters addressed critical manufacturability issues facing us during the coming transition to EUV, complications inherent in triple patterning; and successful approaches to using DfM as part of an overall yield enhancement strategy.

The depth of the technical sessions was also impressive, covering a wide range of topics. Emphasis on double patterning implications was apparent this year, as you might expect given current industry trends. An invited tutorial presentation describing the design flow (tailored to lithographers) was particularly well received. Other topics of note included design rule implications, place and route impact to DfM and variability.

One highlight of the event was the joint session with the Optical Lithography conference. Recognizing the powerful overlap between computational lithography topics like OPC and SMO, two joint sessions were presented featuring papers of mutual interest to both conferences. The standing-room-only crowd is clear evidence that this sort of inter-conference collaboration should continue in the future. Special thanks to the Optical guys for making this happen.

The bottom line is that the conference was very successful by any measure. As a personal note, I would like to thank the authors and conference attendees for their active participation: this conference is for you, and you make it happen.

Of course none of this would be possible without the generous support (and patience) of my co-chair (John Sturtevant of Mentor Graphics) and SPIE staff. Further, I deeply appreciate the efforts of the conference program committee for all their help in putting the program together and chairing sessions.

Together with these excellent people, I am already working hard to put together an even better program for 2013. I cannot wait to see you there.

Mark E. Mason
John L. Sturtevant